

ABSTRACT

Silicon oxide etching solutions containing the product of at least one bifluoride source
5 compound dissolved in a solvent consisting of at least one carboxylic acid, and further
comprising from about 0.5 to about 3 percent by solution weight of hydrofluoric acid and
from about 1 to about 5 percent by solution weight of water, wherein the total concentration
of bifluoride source compound is between about 1.25 and about 5.0 moles per kilogram of
solvent. Methods for selectively removing silicon oxides and metal silicates from metal
10 surfaces are also disclosed.